STMicroelectronics - STM32F401CCY6TR Datasheet

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"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	84MHz
Connectivity	I²C, IrDA, LINbus, SDIO, SPI, UART/USART, USB OTG
Peripherals	Brown-out Detect/Reset, DMA, I²S, POR, PWM, WDT
Number of I/O	36
Program Memory Size	256KB (256K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	64K x 8
Voltage - Supply (Vcc/Vdd)	1.7V ~ 3.6V
Data Converters	A/D 10x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	49-UFBGA, WLCSP
Supplier Device Package	49-WLCSP
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f401ccy6tr

3.15.1 Regulator ON

On packages embedding the BYPASS_REG pin, the regulator is enabled by holding BYPASS_REG low. On all other packages, the regulator is always enabled.

There are three power modes configured by software when the regulator is ON:

- MR is used in the nominal regulation mode (With different voltage scaling in Run)

  In Main regulator mode (MR mode), different voltage scaling are provided to reach the best compromise between maximum frequency and dynamic power consumption.
- LPR is used in the Stop modes

  The LP regulator mode is configured by software when entering Stop mode.
- Power-down is used in Standby mode.

  The Power-down mode is activated only when entering in Standby mode. The regulator output is in high impedance and the kernel circuitry is powered down, inducing zero consumption. The contents of the registers and SRAM are lost.

Depending on the package, one or two external ceramic capacitors should be connected on the V_{CAP_1} and V_{CAP_2} pins. The V_{CAP_2} pin is only available for the LQFP100 and UFBGA100 packages.

All packages have the regulator ON feature.

3.15.2 Regulator OFF

The Regulator OFF is available only on the UFBGA100, which features the BYPASS_REG pin. The regulator is disabled by holding BYPASS_REG high. The regulator OFF mode allows to supply externally a V12 voltage source through V_{CAP_1} and V_{CAP_2} pins.

Since the internal voltage scaling is not managed internally, the external voltage value must be aligned with the targeted maximum frequency. Refer to *Table 14: General operating conditions*.

The two 2.2 µF V_{CAP} ceramic capacitors should be replaced by two 100 nF decoupling capacitors. Refer to *Figure 18: Power supply scheme*.

When the regulator is OFF, there is no more internal monitoring on V12. An external power supply supervisor should be used to monitor the V12 of the logic power domain. PA0 pin should be used for this purpose, and act as power-on reset on V12 power domain.

In regulator OFF mode, the following features are no more supported:

- PA0 cannot be used as a GPIO pin since it allows to reset a part of the V12 logic power domain which is not reset by the NRST pin.
- As long as PA0 is kept low, the debug mode cannot be used under power-on reset. As a consequence, PA0 and NRST pins must be managed separately if the debug connection under reset or pre-reset is required.

Table 8. STM32F401xB/STM32F401xC pin definitions (continued)

Pin Number					Pin name (function after reset)[1]	Pin type	I/O structure	Notes	Alternate functions	Additional functions
UQFN48	WLCSP49	LQFP64	LQFP100	UFBGA100						
-	-	-	45	M11	PE14	I/O	FT	-	SPI4_MOSI, TIM1_CH4, EVENTOUT	-
-	-	-	46	M12	PE15	I/O	FT	-	TIM1_BKIN, EVENTOUT	-
21	E3	29	47	L10	PB10	I/O	FT	-	SPI2_SCK/I2S2_CK, I2C2_SCL, TIM2_CH3, EVENTOUT	-
-	-	-	-	K9	PB11	I/O	FT	-	TIM2_CH4, I2C2_SDA, EVENTOUT	-
22	G2	30	48	L11	VCAP_1	S	-	-	-	-
23	D3	31	49	F12	VSS	S	-	-	-	-
24	F2	32	50	G12	VDD	S	-	-	-	-
25	E2	33	51	L12	PB12	I/O	FT	-	SPI2_NSS/I2S2_WS, I2C2_SMBA, TIM1_BKIN, EVENTOUT	-
26	G1	34	52	K12	PB13	I/O	FT	-	SPI2_SCK/I2S2_CK, TIM1_CH1N, EVENTOUT	-
27	F1	35	53	K11	PB14	I/O	FT	-	SPI2_MISO, I2S2ext_SD, TIM1_CH2N, EVENTOUT	-
28	E1	36	54	K10	PB15	I/O	FT	-	SPI2_MOSI/I2S2_SD, TIM1_CH3N, EVENTOUT	RTC_REFIN
-	-	-	55	-	PD8	I/O	FT	-	EVENTOUT	-
-	-	-	56	K8	PD9	I/O	FT	-	EVENTOUT	-
-	-	-	57	J12	PD10	I/O	FT	-	EVENTOUT	-
-	-	-	58	J11	PD11	I/O	FT	-	EVENTOUT	-
-	-	-	59	J10	PD12	I/O	FT	-	TIM4_CH1, EVENTOUT	-
-	-	-	60	H12	PD13	I/O	FT	-	TIM4_CH2, EVENTOUT	-
-	-	-	61	H11	PD14	I/O	FT	-	TIM4_CH3, EVENTOUT	-
-	-	-	62	H10	PD15	I/O	FT	-	TIM4_CH4, EVENTOUT	-
-	-	37	63	E12	PC6	I/O	FT	-	I2S2_MCK, USART6_TX, TIM3_CH1, SDIO_D6, EVENTOUT	-
-	-	38	64	E11	PC7	I/O	FT	-	I2S3_MCK, USART6_RX, TIM3_CH2, SDIO_D7, EVENTOUT	-

6 Electrical characteristics

6.1 Parameter conditions

Unless otherwise specified, all voltages are referenced to V_{SS}.

6.1.1 Minimum and maximum values

Unless otherwise specified the minimum and maximum values are guaranteed in the worst conditions of ambient temperature, supply voltage and frequencies by tests in production on 100% of the devices with an ambient temperature at T_A = 25 °C and T_A = $T_A$max (given by the selected temperature range).

Data based on characterization results, design simulation and/or technology characteristics are indicated in the table footnotes and are not tested in production. Based on characterization, the minimum and maximum values refer to sample tests and represent the mean value plus or minus three times the standard deviation (mean ±3 σ).

6.1.2 Typical values

Unless otherwise specified, typical data are based on T_A = 25 °C, V_{DD} = 3.3 V (for the 1.7 V ≤V_{DD} ≤3.6 V voltage range). They are given only as design guidelines and are not tested.

Typical ADC accuracy values are determined by characterization of a batch of samples from a standard diffusion lot over the full temperature range, where 95% of the devices have an error less than or equal to the value indicated (mean ±2 σ).

6.1.3 Typical curves

Unless otherwise specified, all typical curves are given only as design guidelines and are not tested.

6.1.4 Loading capacitor

The loading conditions used for pin parameter measurement are shown in *Figure 16*.

Figure 16. Pin loading conditions

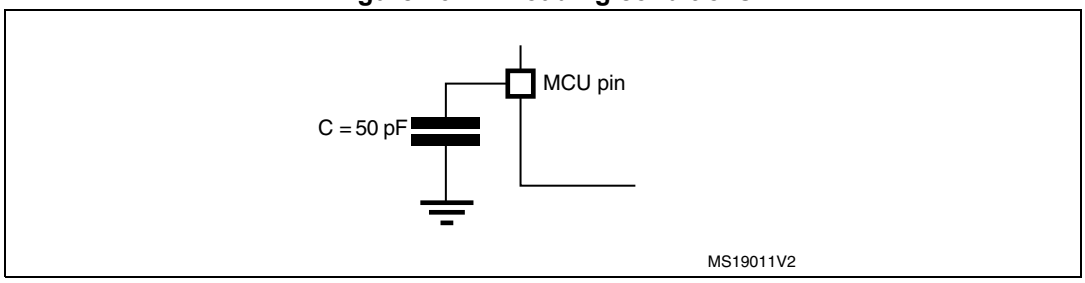


Table 14. General operating conditions (continued)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
T_A	Ambient temperature for 6 suffix version	Maximum power dissipation	–40	-	85	°C
		Low power dissipation(8)	–40	-	105	
	Ambient temperature for 7 suffix version	Maximum power dissipation	–40	-	105	
		Low power dissipation(8)	–40	-	125	
T_J	Junction temperature range	6 suffix version	–40	-	105	
		7 suffix version	–40	-	125	

1. V_{DD}/V_{DDA} minimum value of 1.7 V with the use of an external power supply supervisor (refer to *Section 3.14.2: Internal reset OFF*).
2. When the ADC is used, refer to *Table 66: ADC characteristics*.
3. If V_{REF+} pin is present, it must respect the following condition: V_{DDA}-V_{REF+} < 1.2 V.
4. It is recommended to power V_{DD} and V_{DDA} from the same source. A maximum difference of 300 mV between V_{DD} and V_{DDA} can be tolerated during power-up and power-down operation.
5. Guaranteed by test in production
6. To sustain a voltage higher than VDD+0.3, the internal Pull-up and Pull-Down resistors must be disabled
7. If T_A is lower, higher P_D values are allowed as long as T_J does not exceed T_{Jmax}.
8. In low power dissipation state, T_A can be extended to this range as long as T_J does not exceed T_{Jmax}.

Table 15. Features depending on the operating power supply range

Operating power supply range	ADC operation	Maximum Flash memory access frequency with no wait states ($f_{Flashmax}$)	Maximum Flash memory access frequency with wait states (1)(2)	I/O operation	Clock output frequency on I/O pins(3)	Possible Flash memory operations
V_{DD} =1.7 to 2.1 V(4)	Conversion time up to 1.2 Msps	20 MHz(5)	84 MHz with 4 wait states	– No I/O compensation	up to 30 MHz	8-bit erase and program operations only
V_{DD} = 2.1 to 2.4 V	Conversion time up to 1.2 Msps	22 MHz	84 MHz with 3 wait states	– No I/O compensation	up to 30 MHz	16-bit erase and program operations
V_{DD} = 2.4 to 2.7 V	Conversion time up to 2.4 Msps	24 MHz	84 MHz with 3 wait states	– I/O compensation works	up to 48 MHz	16-bit erase and program operations
V_{DD} = 2.7 to 3.6 V(6)	Conversion time up to 2.4 Msps	30 MHz	84 MHz with 2 wait states	– I/O compensation works	– up to 84 MHz when V_{DD} = 3.0 to 3.6 V – up to 48 MHz when V_{DD} = 2.7 to 3.0 V	32-bit erase and program operations

Table 30. Typical and maximum current consumption in Standby mode - V_{DD}=3.3 V

Symbol	Parameter	Conditions	Typ(1)	Max(2)			Unit
			T_A = 25 °C	T_A = 25 °C	T_A = 85 °C	T_A = 105 °C	
I_{DD_STBY}	Supply current in Standby mode	Low-speed oscillator (LSE) and RTC ON	2.8	5.0	14.0	28.0	µA
		RTC and LSE OFF	2.1	4.0(3)	13.0	27.0(3)	

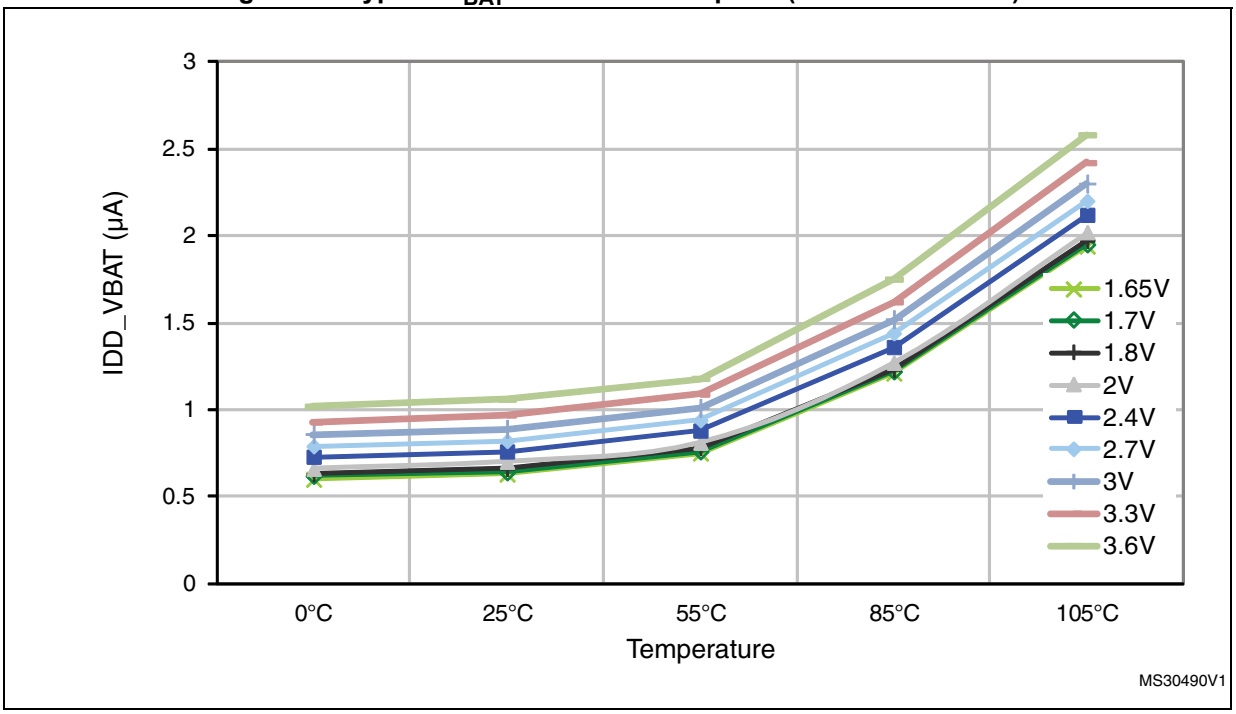
1. When the PDR is OFF (internal reset is OFF), the typical current consumption is reduced by 1.2 µA.
2. Guaranteed by characterization, unless otherwise specified.
3. Guaranteed by test in production.

Table 31. Typical and maximum current consumptions in V_{BAT} mode

Symbol	Parameter	Conditions(1)	Typ			Max(2)		Unit
			T_A = 25 °C			T_A = 85 °C	T_A = 105 °C	
			V_{BAT} = 1.7 V	V_{BAT}= 2.4 V	V_{BAT} = 3.3 V	V_{BAT} = 3.6 V		
I_{DD_VBAT}	Backup domain supply current	Low-speed oscillator (LSE) and RTC ON	0.66	0.76	0.97	3.0	5.0	µA
		RTC and LSE OFF	0.1	0.1	0.1	2.0	4.0	

1. Crystal used: Abracon ABS07-120-32.768 kHz-T with a C_L of 6 pF for typical values.
2. Guaranteed by characterization.

Figure 21. Typical V_{BAT} current consumption (LSE and RTC ON)



I/O system current consumption

The current consumption of the I/O system has two components: static and dynamic.

I/O static current consumption

All the I/Os used as inputs with pull-up generate current consumption when the pin is externally held low. The value of this current consumption can be simply computed by using the pull-up/pull-down resistors values given in *Table 54: I/O static characteristics*.

For the output pins, any external pull-down or external load must also be considered to estimate the current consumption.

Additional I/O current consumption is due to I/Os configured as inputs if an intermediate voltage level is externally applied. This current consumption is caused by the input Schmitt trigger circuits used to discriminate the input value. Unless this specific configuration is required by the application, this supply current consumption can be avoided by configuring these I/Os in analog mode. This is notably the case of ADC input pins which should be configured as analog inputs.

Caution: Any floating input pin can also settle to an intermediate voltage level or switch inadvertently, as a result of external electromagnetic noise. To avoid current consumption related to floating pins, they must either be configured in analog mode, or forced internally to a definite digital value. This can be done either by using pull-up/down resistors or by configuring the pins in output mode.

I/O dynamic current consumption

In addition to the internal peripheral current consumption (see *Table 33: Peripheral current consumption*), the I/Os used by an application also contribute to the current consumption. When an I/O pin switches, it uses the current from the MCU supply voltage to supply the I/O pin circuitry and to charge/discharge the capacitive load (internal or external) connected to the pin:

$$I_{SW} = V_{DD} \times f_{SW} \times C$$

where

I_{SW} is the current sunk by a switching I/O to charge/discharge the capacitive load

V_{DD} is the MCU supply voltage

f_{SW} is the I/O switching frequency

C is the total capacitance seen by the I/O pin: $C = C_{INT} + C_{EXT}$

The test pin is configured in push-pull output mode and is toggled by software at a fixed frequency.

On-chip peripheral current consumption

The MCU is placed under the following conditions:

- At startup, all I/O pins are in analog input configuration.
- All peripherals are disabled unless otherwise mentioned.
- The ART accelerator is ON.
- Voltage Scale 2 mode selected, internal digital voltage V12 = 1.26 V.
- HCLK is the system clock at 84 MHz. $f_{PCLK1} = f_{HCLK}/2$, and $f_{PCLK2} = f_{HCLK}$.
  The given value is calculated by measuring the difference of current consumption
  - with all peripherals clocked off
  - with only one peripheral clocked on
- Ambient operating temperature is 25 °C and V_{DD}=3.3 V.

Table 33. Peripheral current consumption

Peripheral		I_{DD} (typ)	Unit
AHB1 (up to 84MHz)	GPIOA	1.55	µA/MHz
	GPIOB	1.55	
	GPIOC	1.55	
	GPIOD	1.55	
	GPIOE	1.55	
	GPIOH	1.55	
	CRC	0.36	
	DMA1	20.24	
	DMA2	21.07	
APB1 (up to 42MHz)	TIM2	11.19	µA/MHz
	TIM3	8.57	
	TIM4	8.33	
	TIM5	11.19	
	PWR	0.71	
	USART2	3.33	
	I2C1/2/3	3.10	
	SPI2(1)	2.62	
	SPI3(1)	2.86	
	I2S2	1.90	
	I2S3	1.67	
	WWDG	0.71	
AHB2 (up to 84MHz)	OTG_FS	23.93	µA/MHz

Figure 28 and *Figure 29* show the main PLL output clock waveforms in center spread and down spread modes, where:

F0 is f_{PLL_OUT} nominal.

T_{mode} is the modulation period.

md is the modulation depth.

Figure 28. PLL output clock waveforms in center spread mode

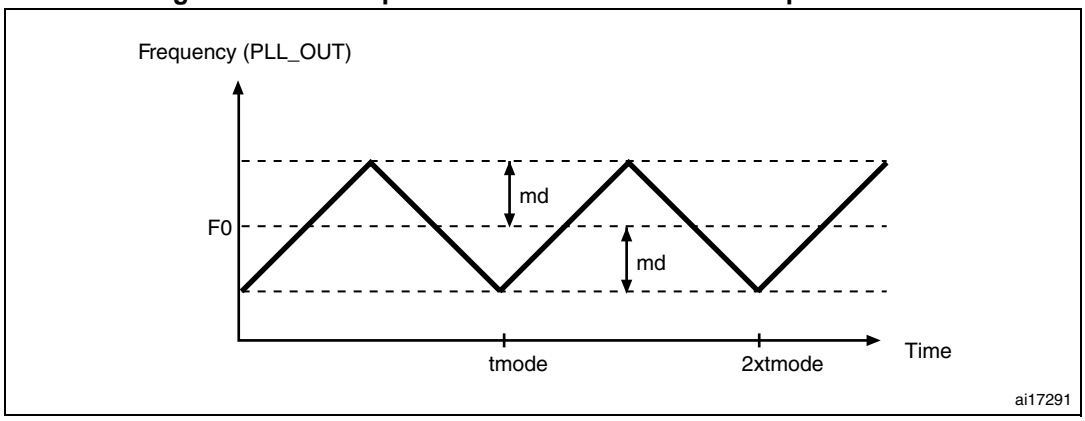
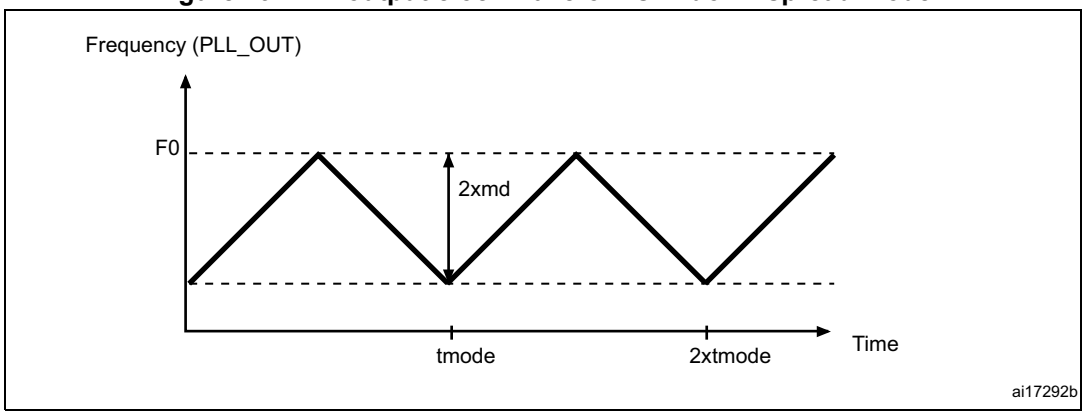


Figure 29. PLL output clock waveforms in down spread mode



6.3.12 Memory characteristics

Flash memory

The characteristics are given at T_A = –40 to 105 °C unless otherwise specified.

The devices are shipped to customers with the Flash memory erased.

Table 44. Flash memory characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
I_{DD}	Supply current	Write / Erase 8-bit mode, V_{DD} = 1.7 V	-	5	-	mA
		Write / Erase 16-bit mode, V_{DD} = 2.1 V	-	8	-	
		Write / Erase 32-bit mode, V_{DD} = 3.3 V	-	12	-	

Electromagnetic Interference (EMI)

The electromagnetic field emitted by the device are monitored while a simple application, executing EEMBC code, is running. This emission test is compliant with SAE IEC61967-2 standard which specifies the test board and the pin loading.

Table 49. EMI characteristics for WLCSP49

Symbol	Parameter	Conditions	Monitored frequency band	Max vs. [f_{HSE}/f_{CPU}]	Unit
				25/84 MHz	
S_{EMI}	Peak level	V_{DD} = 3.3 V, T_A = 25 °C, conforming to IEC61967-2	0.1 to 30 MHz	-6	dBµV
			30 to 130 MHz	-6	
			130 MHz to 1 GHz	-10	
			SAE EMI Level	1.5	-

Table 50. EMI characteristics for LQFP100

Symbol	Parameter	Conditions	Monitored frequency band	Max vs. [f_{HSE}/f_{CPU}]	Unit
				25/84 MHz	
S_{EMI}	Peak level	V_{DD} = 3.3 V, T_A = 25 °C, conforming to IEC61967-2	0.1 to 30 MHz	18	dBµV
			30 to 130 MHz	23	
			130 MHz to 1 GHz	12	
			SAE EMI Level	3.5	-

6.3.14 Absolute maximum ratings (electrical sensitivity)

Based on three different tests (ESD, LU) using specific measurement methods, the device is stressed in order to determine its performance in terms of electrical sensitivity.

Electrostatic discharge (ESD)

Electrostatic discharges (a positive then a negative pulse separated by 1 second) are applied to the pins of each sample according to each pin combination. The sample size depends on the number of supply pins in the device (3 parts × (n+1) supply pins). This test conforms to the JESD22-A114/C101 standard.

Table 51. ESD absolute maximum ratings

Symbol	Ratings	Conditions	Class	Maximum value(1)	Unit
$V_{ESD(HBM)}$	Electrostatic discharge voltage (human body model)	T_A = +25 °C conforming to JESD22-A114	2	2000	V
$V_{ESD(CDM)}$	Electrostatic discharge voltage (charge device model)	T_A = +25 °C conforming to ANSI/ESD STM5.3.1	II	500	

1. Guaranteed by characterization.

Static latchup

Two complementary static tests are required on six parts to assess the latchup performance:

- A supply overvoltage is applied to each power supply pin
- A current injection is applied to each input, output and configurable I/O pin

These tests are compliant with EIA/JESD 78A IC latchup standard.

Table 52. Electrical sensitivities

Symbol	Parameter	Conditions	Class
LU	Static latch-up class	T_A = +105 °C conforming to JESD78A	II level A

6.3.15 I/O current injection characteristics

As a general rule, current injection to the I/O pins, due to external voltage below V_{SS} or above V_{DD} (for standard, 3 V-capable I/O pins) should be avoided during normal product operation. However, in order to give an indication of the robustness of the microcontroller in cases when abnormal injection accidentally happens, susceptibility tests are performed on a sample basis during device characterization.

Functional susceptibilty to I/O current injection

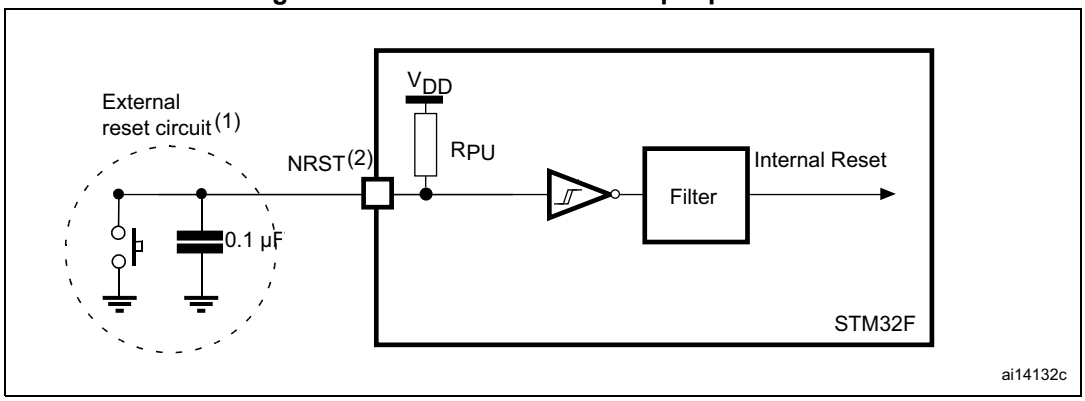
While a simple application is executed on the device, the device is stressed by injecting current into the I/O pins programmed in floating input mode. While current is injected into the I/O pin, one at a time, the device is checked for functional failures.

The failure is indicated by an out of range parameter: ADC error above a certain limit (>5 LSB TUE), out of conventional limits of induced leakage current on adjacent pins (out of –5 µA/+0 µA range), or other functional failure (for example reset, oscillator frequency deviation).

Negative induced leakage current is caused by negative injection and positive induced leakage current by positive injection.

The test results are given in *Table 53*.

Figure 32. Recommended NRST pin protection



1. The reset network protects the device against parasitic resets.
2. The external capacitor must be placed as close as possible to the device.
3. The user must ensure that the level on the NRST pin can go below the $V_{IL(NRST)}$ max level specified in *Table 57*. Otherwise the reset is not taken into account by the device.

6.3.18 TIM timer characteristics

The parameters given in *Table 58* are guaranteed by design.

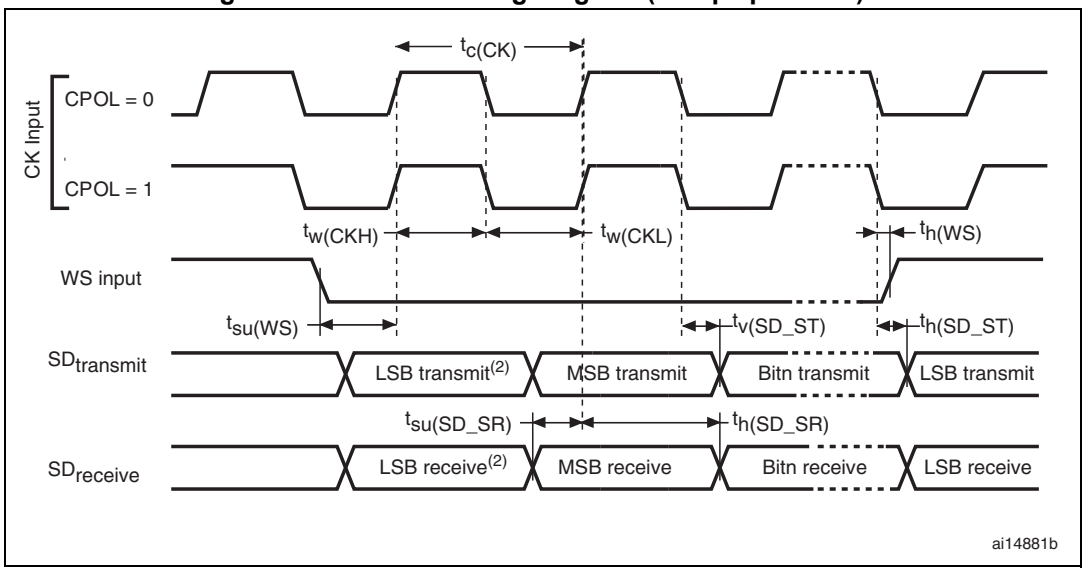
Refer to *Section 6.3.16: I/O port characteristics* for details on the input/output alternate function characteristics (output compare, input capture, external clock, PWM output).

Table 58. TIMx characteristics(1)(2)

Symbol	Parameter	Conditions(3)	Min	Max	Unit
$t_{res(TIM)}$	Timer resolution time	AHB/APBx prescaler=1 or 2 or 4, $f_{TIMxCLK}$ = 84 MHz	1	-	$t_{TIMxCLK}$
			11.9	-	ns
		AHB/APBx prescaler>4, $f_{TIMxCLK}$ = 84 MHz	1	-	$t_{TIMxCLK}$
			11.9	-	ns
f_{EXT}	Timer external clock frequency on CH1 to CH4	$f_{TIMxCLK}$ = 84 MHz	0	$f_{TIMxCLK}/2$	MHz
			0	42	MHz
Res_{TIM}	Timer resolution		-	16/32	bit
$t_{COUNTER}$	16-bit counter clock period when internal clock is selected	$f_{TIMxCLK}$ = 84 MHz	0.0119	780	µs
t_{MAX_COUNT}	Maximum possible count with 32-bit counter		-	65536 × 65536	$t_{TIMxCLK}$
		$f_{TIMxCLK}$ = 84 MHz	-	51.1	S

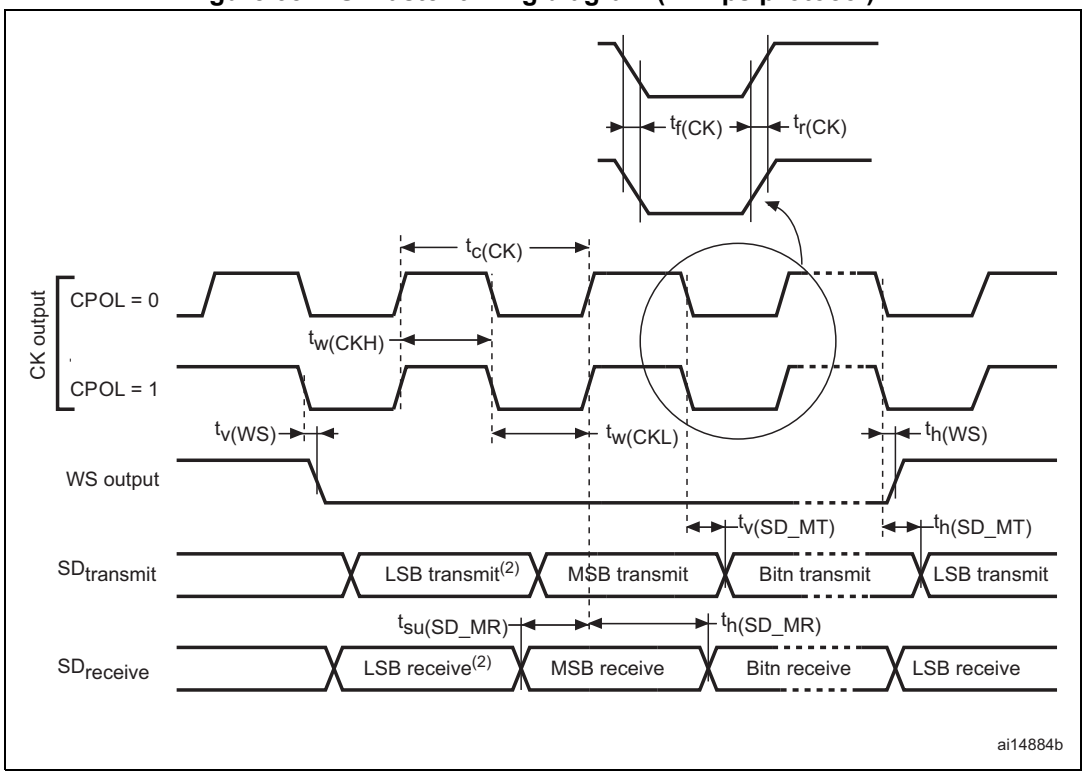
1. TIMx is used as a general term to refer to the TIM1 to TIM11 timers.
2. Guaranteed by design.
3. The maximum timer frequency on APB1 is 42 MHz and on APB2 is up to 84 MHz, by setting the TIMPRE bit in the RCC_DCKCFGR register, if APBx prescaler is 1 or 2 or 4, then TIMxCLK = HCKL, otherwise TIMxCLK >= 4x PCLKx.

Figure 37. I²S slave timing diagram (Philips protocol)(1)



1. LSB transmit/receive of the previously transmitted byte. No LSB transmit/receive is sent before the first byte.

Figure 38. I²S master timing diagram (Philips protocol)(1)



1. LSB transmit/receive of the previously transmitted byte. No LSB transmit/receive is sent before the first byte.

Refer to *Section 6.3.16: I/O port characteristics* for more details on the input/output characteristics.

Figure 44. SDIO high-speed mode

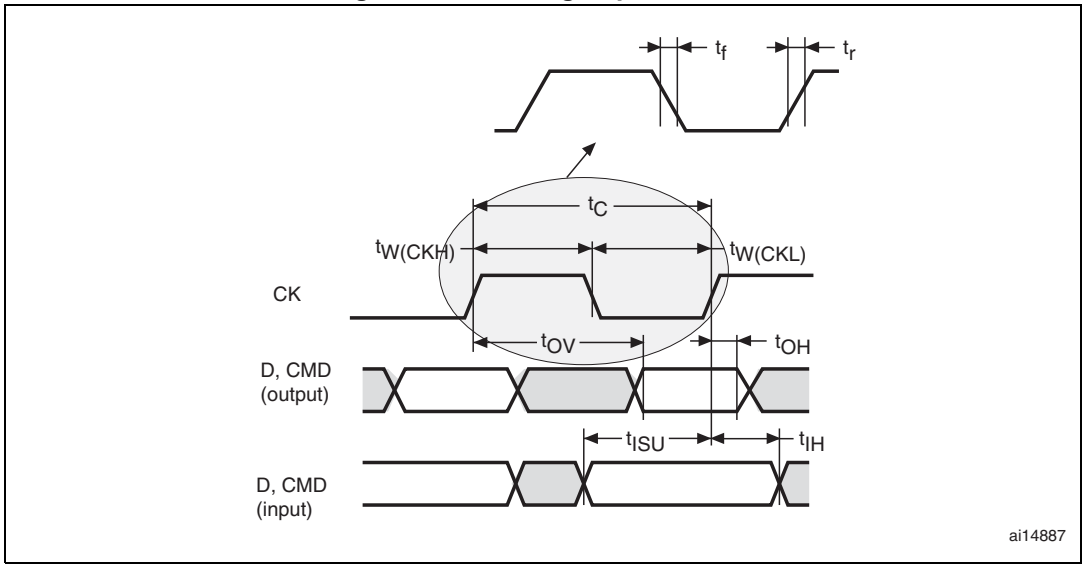


Figure 45. SD default mode

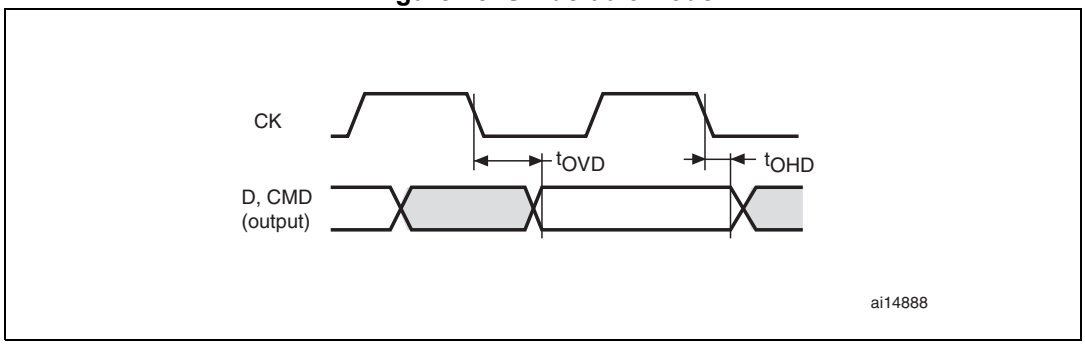


Table 77. Dynamic characteristics: SD / MMC characteristics(1)(2)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{PP}	Clock frequency in data transfer mode		0	-	48	MHz
-	SDIO_CK/fPCLK2 frequency ratio		-	-	8/3	-
$t_{W(CKL)}$	Clock low time	fpp = 48MHz	8.5	9	-	ns
$t_{W(CKH)}$	Clock high time	fpp = 48MHz	8.3	10	-	
CMD, D inputs (referenced to CK) in MMC and SD HS mode						
t_{ISU}	Input setup time HS	fpp = 48MHz	3.5	-	-	ns
t_{IH}	Input hold time HS	fpp = 48MHz	0	-	-	
CMD, D outputs (referenced to CK) in MMC and SD HS mode						
t_{OV}	Output valid time HS	fpp = 48MHz	-	4.5	7	ns
t_{OH}	Output hold time HS	fpp = 48MHz	3	-	-	

Table 80. WLCSP49 recommended PCB design rules (0.4 mm pitch)

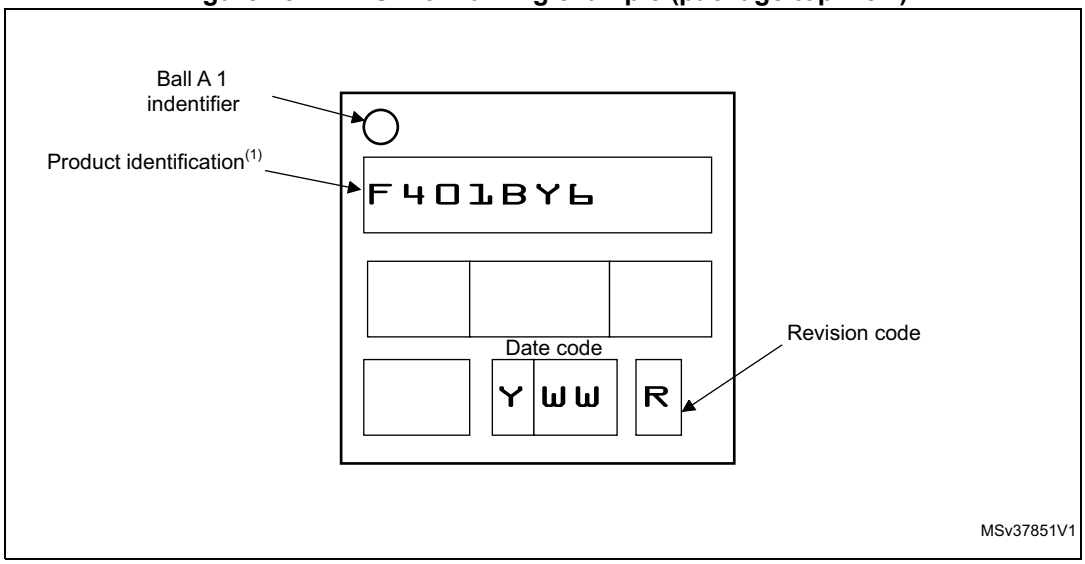
Dimension	Recommended values
Pitch	0.4 mm
Dpad	260 µm max. (circular) 220 µm recommended
Dsm	300 µm min. (for 260 µm diameter pad)
PCB pad design	Non-solder mask defined via underbump allowed

WLCSP49 device marking

The following figure gives an example of topside marking orientation versus ball A1 identifier location.

Other optional marking or inset/upset marks, which depend on supply chain operations, are not indicated below.

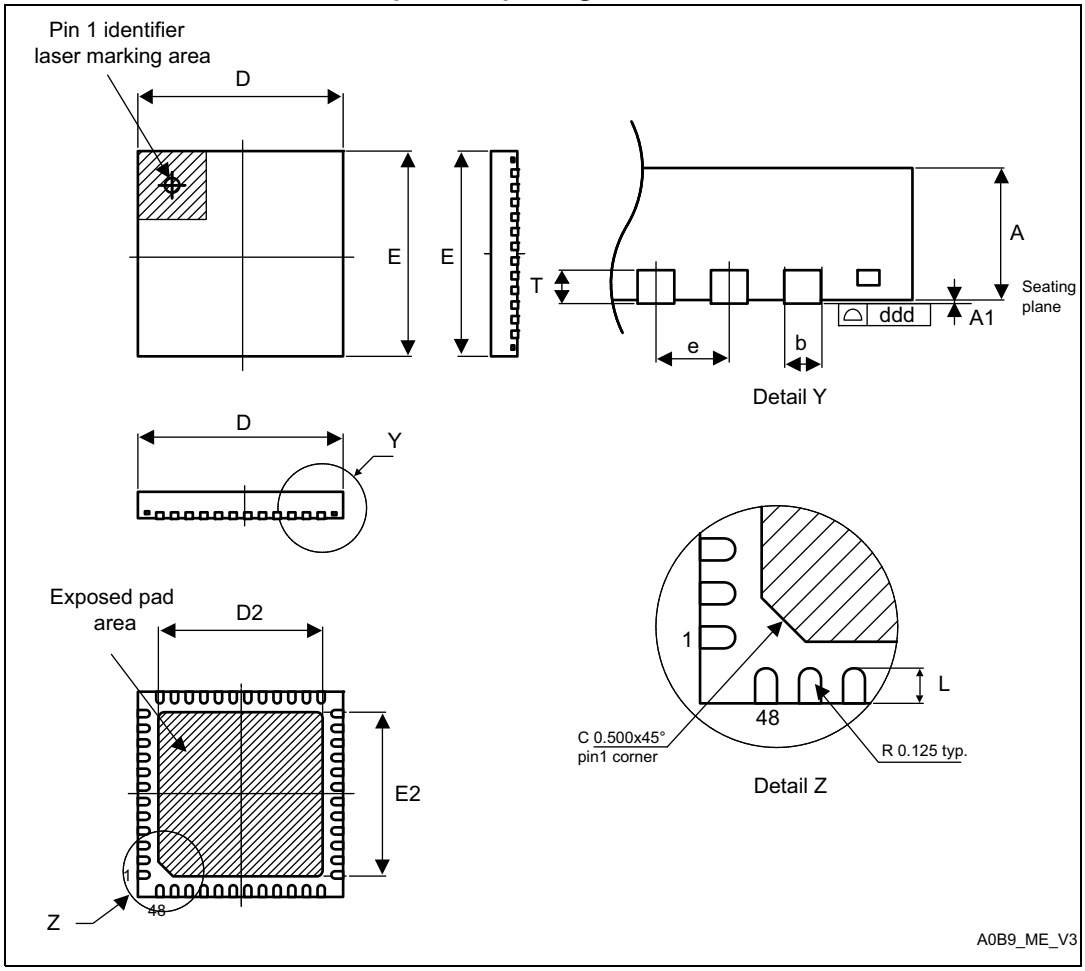
Figure 48. WLCSP49 marking example (package top view)



1. Parts marked as “ES”, “E” or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering samples to run qualification activity.

7.2 UFQFPN48 package information

Figure 49. UFQFPN48 - 48-lead, 7 x 7 mm, 0.5 mm pitch, ultra thin fine pitch quad flat package outline



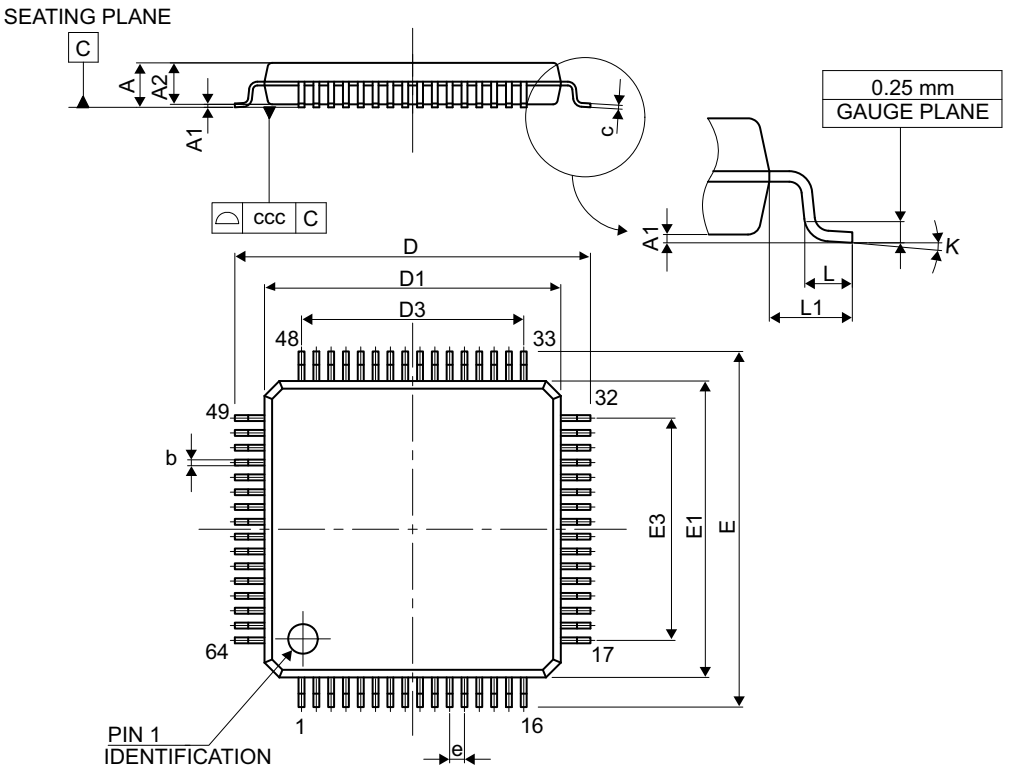
1. Drawing is not to scale.
2. All leads/pads should also be soldered to the PCB to improve the lead/pad solder joint life.
3. There is an exposed die pad on the underside of the UFQFPN package. It is recommended to connect and solder this back-side pad to PCB ground.

Table 81. UFQFPN48 - 48-lead, 7 x 7 mm, 0.5 mm pitch, ultra thin fine pitch quad flat package mechanical data

Symbol	millimeters			inches(1)		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	0.500	0.550	0.600	0.0197	0.0217	0.0236
A1	0.000	0.020	0.050	0.0000	0.0008	0.0020
D	6.900	7.000	7.100	0.2717	0.2756	0.2795
E	6.900	7.000	7.100	0.2717	0.2756	0.2795
D2	5.500	5.600	5.700	0.2165	0.2205	0.2244

7.3 LQFP64 package information

Figure 52. LQFP64 - 64-pin, 10 x 10 mm, 64-pin low-profile quad flat package outline



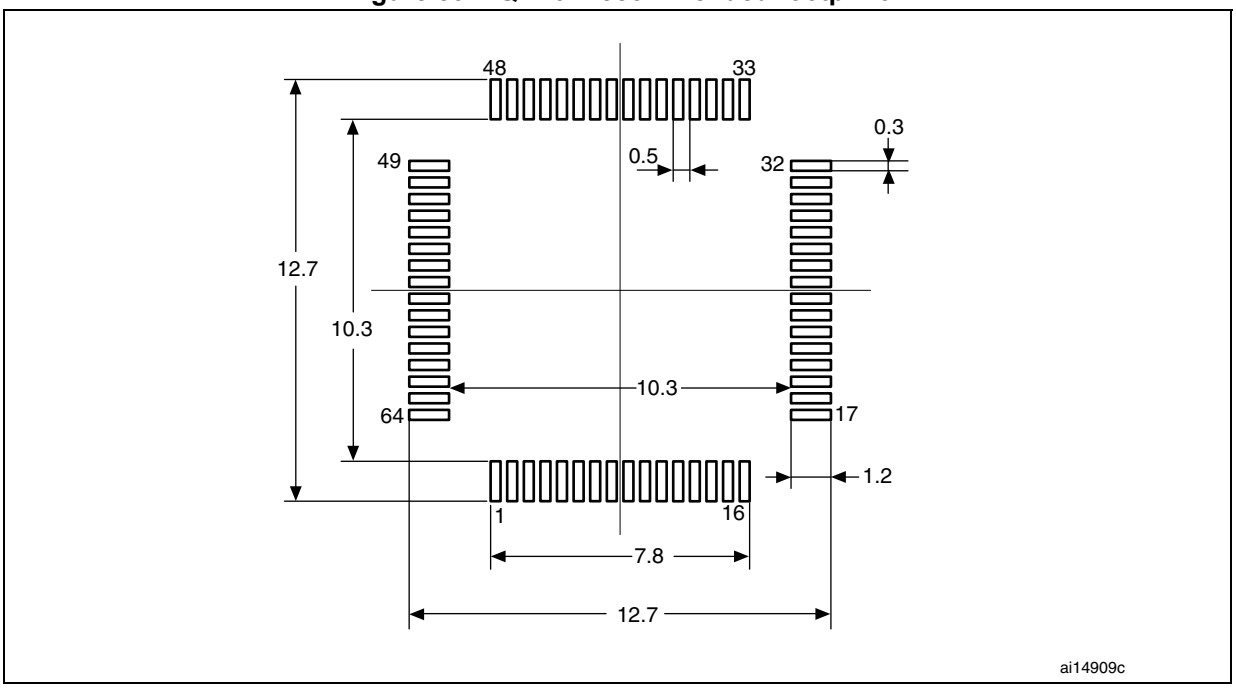
1. Drawing is not to scale.

Table 82. LQFP64 - 64-pin, 10 x 10 mm, 64-pin low-profile quad flat package mechanical data

Symbol	millimeters			inches[1]		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	-	-	1.600	-	-	0.0630
A1	0.050	-	0.150	0.0020	-	0.0059
A2	1.350	1.400	1.450	0.0531	0.0551	0.0571
b	0.170	0.220	0.270	0.0067	0.0087	0.0106
c	0.090	-	0.200	0.0035	-	0.0079
D	-	12.000	-	-	0.4724	-
D1	-	10.000	-	-	0.3937	-
E	-	12.000	-	-	0.4724	-
E1	-	10.000	-	-	0.3937	-
E3	-	7.5000	-	-	0.2953	-
e	-	0.500	-	-	0.0197	-
K	0°	3.5°	7°	0°	3.5°	7°
L	0.450	0.600	0.750	0.0177	0.0236	0.0295
L1	-	1.000	-	-	0.0394	-
ccc	-	-	0.080	-	-	0.0031

1. Values in inches are converted from mm and rounded to 4 decimal digits.

Figure 53. LQFP64 recommended footprint



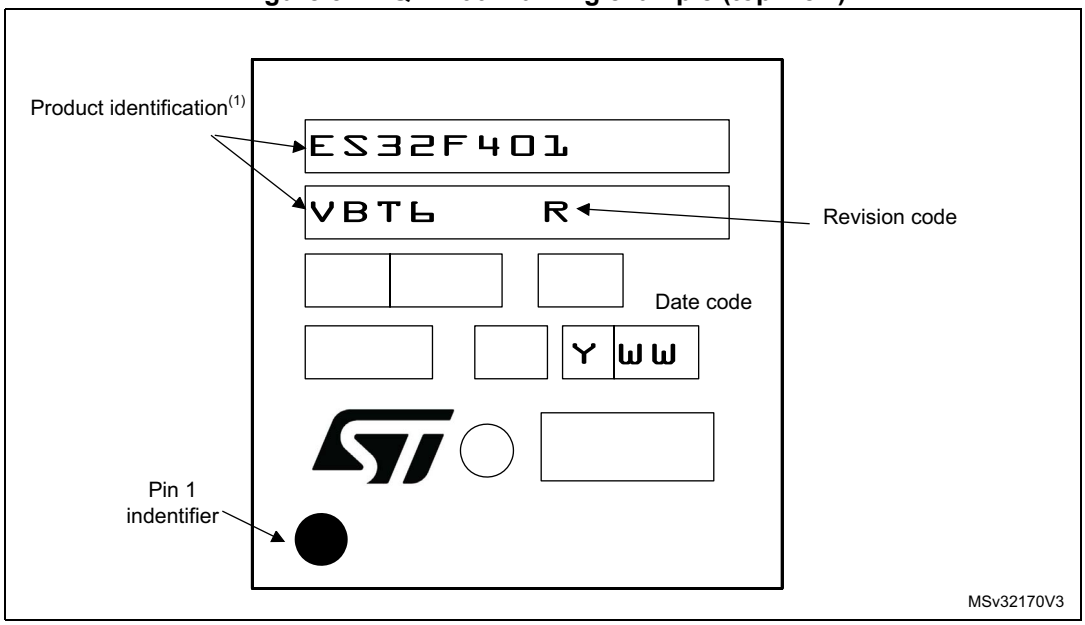
1. Dimensions are in millimeters.

LQFP100 device marking

The following figure gives an example of topside marking orientation versus pin 1 identifier location.

Other optional marking or inset/upset marks, which depend on supply chain operations, are not indicated below.

Figure 57. LQPF100 marking example (top view)



1. Parts marked as “ES”, “E” or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering samples to run qualification activity.

8 Part numbering

Table 87. Ordering information scheme

Example: STM32 F 401 C C T 6 xxx

Device family

STM32 = ARM-based 32-bit microcontroller

Product type

F = General-purpose

Device subfamily

401: 401 family

Pin count

C = 48/49 pins

R = 64 pins

V = 100 pins

Flash memory size

B = 128 Kbytes of Flash memory

C = 256 Kbytes of Flash memory

Package

H = UFBGA

T = LQFP

U = UFQFPN

Y = WLCSP

Temperature range

6 = Industrial temperature range, –40 to 85 °C

7 = Industrial temperature range, –40 to 105 °C

Packing

TR = tape and reel

TT = tape and reel for WLCSP as per PCN9547(1)

No character = tray or tube

1. To get this document, please contact your nearest ST Sales Office.